

**Notice of References Cited**

Application/Control No.

09/772,858

Applicant(s)/Patent Under  
Reexamination  
KAMIJIMA, AKIFUMI

Examiner

Allan W. Olsen

Art Unit

1763

Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-4,592,801	06-1986	Hara et al.	216/22
	B	US-5,316,617	05-1994	Kawabe et al.	216/22
	C	US-5,506,197	04-1996	Nakamura et al.	505/193
	D	US-6,304,784	10-2001	Allee et al.	607/116
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	JP 01175232 A	07-1989	Japan	TOUNO, HIROE	H01L 21/302
	O	JP 04251853 A	09-1992	Japan	WATABE et al.	G03F 07/075
	P					
	Q					
	R					
	S					
	T					

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Morimoto et al., "A GaAs Metal-Semiconductor Field-Effect Transistor With a Mushroom Gate Fabricated by Mixed Exposure of Focussed Ion Beams"□□J. Vac. Sci. Technology, B, Vol. 5 No. 1 January/February 1987, pages 211-214.□□
	V	
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.